HALOGEN

FREE



## Vishay Semiconductors

# High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



### **DESCRIPTION**

TSHG5410 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### **FEATURES**

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5
Leads with stand-off

• Peak wavelength:  $\lambda_p = 850 \text{ nm}$ 

High reliabilityHigh radiant power

· High radiant intensity

• Angle of half intensity:  $\varphi = \pm 18^{\circ}$ 

Low forward voltage

• Suitable for high pulse current operation

• High modulation bandwidth:  $f_c = 18 \text{ MHz}$ 

Good spectral matching with CMOS cameras

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Halogen-free according to IEC 61249-2-21 definition

#### **APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- · High speed IR data transmission

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)	
TSHG5410	90	± 18	850	20	

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHG5410	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

#### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	Α	
Power dissipation		P <sub>V</sub>	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

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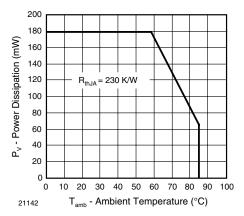


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

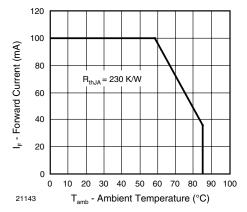


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.5	1.8	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V <sub>F</sub>		2.3		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μΑ
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		125		pF
Dadient intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	le	45	90	135	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	l <sub>e</sub>		900		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φ <sub>e</sub>		55		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 18		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λρ	820	850	880	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		40		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.25		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		20		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		13		ns
Cut-off frequency	I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp	f <sub>c</sub>		18		MHz
Virtual source diameter		d		2.1		mm

## Note

T<sub>amb</sub> = 25 °C, unless otherwise specified



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### **BASIC CHARACTERISTICS**

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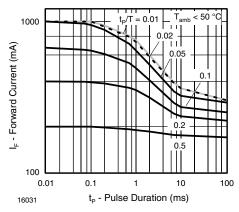


Fig. 3 - Pulse Forward Current vs. Pulse Duration

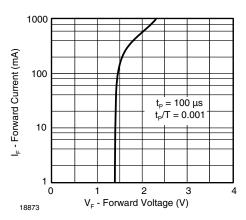


Fig. 4 - Forward Current vs. Forward Voltage

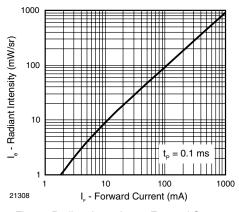


Fig. 5 - Radiant Intensity vs. Forward Current

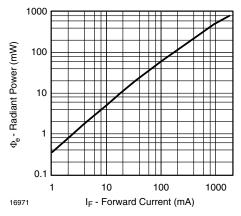


Fig. 6 - Radiant Power vs. Forward Current

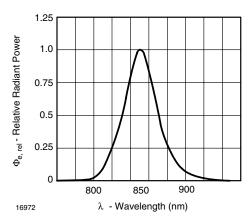


Fig. 7 - Relative Radiant Power vs. Wavelength

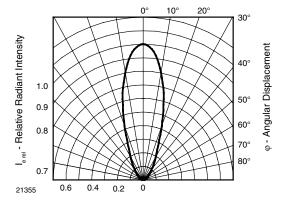
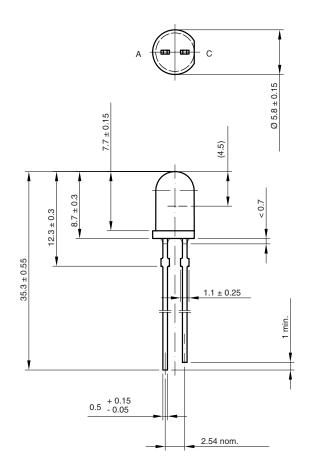


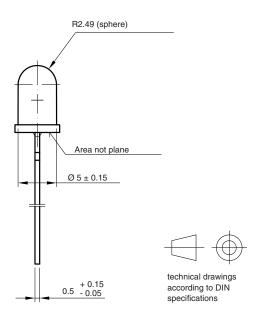
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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## **PACKAGE DIMENSIONS** in millimeters





Drawing-No.: 6.544-5258.11-4 Issue: 2; 19.05.09 21797





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